

|    | Type | Hits | Search Text  | DBs                  | Time Stamp          |
|----|------|------|--|----------------------|---------------------|
| 1  | BRS  | 9    | ("4103342" or "4686552" or "4927779" or "5134616" or "5567962" or "5606189" or "5780335" or "6101117" or "6246083").pn.  | USPAT;<br>US-PGPUB   | 2003/02/26<br>11:11 |
| 2  | BRS  | 0    | kowalshi.in.   | USPAT;<br>US-PGPUB   | 2003/02/26<br>11:12 |
| 3  | BRS  | 532  | kowalski.in.   | USPAT;<br>US-PGPUB   | 2003/02/26<br>11:12 |
| 4  | BRS  | 33   | kowalski.in. and capacitor   | USPAT;<br>US-PGPUB   | 2003/02/26<br>12:16 |
| 5  | IS&R | 10   | ((("4785337") or ("4833094") or ("5384789") or ("4830978") or ("4910567") or ("4916524") or ("5198383") or ("5364808") or ("5468980") or ("5973952"))).PN.   | USPAT;<br>US-PGPUB   | 2003/02/26<br>12:17 |
| 6  | IS&R | 40   | ((("5999440") or ("6207493") or ("4791610") or ("5798545") or ("5317540") or ("5432733") or ("6136652") or ("4864375") or ("4980734") or ("5640350") or ("4388121") or ("4574465") or ("4883543") or ("5208657") or ("5300450") or ("5334548") or ("5383150") or ("5559734") or ("5753420") or ("5999439") or ("4763181") or ("5442211") or ("5618745") or ("6194311") or ("5465249") or ("5872373") or ("6151244") or ("4761385") or ("4786954") or ("4864374") or ("4999811") or ("5365477") or ("5508542") or ("5635419") or ("5671182") or ("5736761") or ("5770510") or ("5866928") or ("5959322") or ("6066870"))).PN. | USPAT;<br>US-PGPUB   | 2003/02/26<br>12:27 |
| 7  | BRS  | 15   | hisamoto.in. and delta   | USPAT;<br>US-PGPUB   | 2003/02/26<br>12:27 |
| 8  | BRS  | 9    | 4103342.URPN.  | USPAT                | 2003/02/26<br>13:45 |
| 9  | BRS  | 3    | ("4103342"   "4715015"   "4792922").PN.  | USPAT                | 2003/02/26<br>13:49 |
| 10 | BRS  | 2    | 5329479.URPN.  | USPAT                | 2003/02/26<br>13:50 |
| 11 | BRS  | 3    | ("3463992"   "3585185"   "3938109").PN.  | USPAT                | 2003/02/26<br>13:52 |
| 12 | BRS  | 3    | ("3463992"   "3585185"   "3938109").PN.  | USPAT                | 2003/02/26<br>13:53 |
| 13 | BRS  | 9    | 4103342.URPN.  | USPAT                | 2003/02/26<br>13:53 |
| 14 | BRS  | 2    | jp-61240497-\$ did. or jp-62065295-\$ did.   | EPO: JPO;<br>DERWENT | 2003/02/26<br>14:09 |

|   | Document ID   | Pages | Title   | Current<br>OR | Current XRef                    | Inventor            |
|---|---------------|-------|---|---------------|---------------------------------|---------------------|
| 1 | US 5329479 A  | 12    | Dynamic semiconductor memories  | 365/149       | 365/206                         | Ota, Yoshiji et al. |
| 2 | US 4888733 A  | 6     | Non-volatile memory cell and sensing method   | 365/145       | 365/149;<br>365/189.07          | Mobley, Kenneth J.  |
| 3 | US 6198151 B1 | 22    | Semiconductor device, semiconductor integrated circuit device, and method of manufacturing same | 257/520       | 257/301;<br>257/E27.084         | Wada, Toshio        |
| 4 | US 5943279 A  | 8     | Semiconductor memory integrated circuit   | 365/205       | 365/149;<br>365/207;<br>365/208 | Wada, Toshio        |

|   | Document ID  | Pages | Title   | Current OR | Current XRef   | Inventor                       |
|---|--------------|-------|---|------------|--|--------------------------------|
| 1 | US 5567962 A | 55    | Semiconductor memory device                           | 257/296    | 257/306;<br>257/530;<br>257/E27.078;<br>257/E27.085;<br>257/E27.103;<br>257/E29.13 | Miyawaki, Mamoru et al.        |
| 2 | US 4103342 A | 6     | Two-device memory cell with single floating capacitor | 365/149    | 365/208  | Miersch, Ekkehard Fritz et al. |

Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/064,869 on February 20, 2003

Combined Classifications

16 365/149  
9 257/296  
9 257/304  
8 257/302  
6 257/301  
6 257/E27.092  
5 257/305  
5 257/E27.085  
4 257/300  
4 257/E27.084  
4 257/E27.086  
4 365/174  
4 365/51  
4 438/243  
4 438/386  
3 257/68  
3 257/E27.093  
3 257/E29.346  
3 365/226  
3 438/242  
3 438/246  
2 257/303  
2 257/347  
2 257/382  
2 257/390  
2 257/905  
2 257/906  
2 257/907  
2 257/E27.075  
2 257/E27.091  
2 257/E27.112  
2 365/145  
2 365/177  
2 365/180  
2 365/189.01  
2 365/189.05  
2 365/63  
2 365/69  
2 365/72  
2 438/248  
2 438/249  
2 438/250  
2 438/253  
2 438/262  
2 438/449  
2 438/554

- 16 365/149 (6 OR, 10 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/129 SYSTEMS USING PARTICULAR ELEMENT  
365/149 Capacitors
- 9 257/296 (4 OR, 5 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 (E) FIELD EFFECT Device  
257/288 (E) Having insulated electrode (e.g., MOSFET,  
MOS diode)  
257/296 (E) Insulated gate capacitor or insulated  
gate transistor combined with capacitor (e.g., dynamic  
memory cell)
- 9 257/304 (2 OR, 7 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 (E) FIELD EFFECT Device  
257/288 (E) Having insulated electrode (e.g., MOSFET,  
MOS diode)  
257/296 (E) Insulated gate capacitor or insulated  
gate transistor combined with capacitor (e.g., dynamic  
memory cell)  
257/301 ...Capacitor in trench  
257/304 ...Storage node isolated by dielectric from  
semiconductor substrate
- 8 257/302 (3 OR, 5 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 (E) FIELD EFFECT Device  
257/288 (E) Having insulated electrode (e.g., MOSFET,  
MOS diode)  
257/296 (E) Insulated gate capacitor or insulated  
gate transistor combined with capacitor (e.g., dynamic  
memory cell)  
257/301 ...Capacitor in trench  
257/302 ...Vertical transistor
- 6 257/301 (5 OR, 1 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 (E) FIELD EFFECT Device  
257/288 (E) Having insulated electrode (e.g., MOSFET,  
MOS diode)  
257/296 (E) Insulated gate capacitor or insulated  
gate transistor combined with capacitor (e.g., dynamic  
memory cell)  
257/301 ...Capacitor in trench
- 6 257/E27.092 (0 OR, 6 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/E27.001 DEVICE CONSISTING OF A PLURALITY OF  
SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR  
ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE  
(EPO)  
257/E27.009 Including semiconductor component with at  
least one potential barrier or surface barrier adapted for  
rectifying, oscillating, amplifying, or switching, or

including integrated passive circuit elements (EPO)  
257/E27.01 ...With semiconductor substrate only (EPO)  
257/E27.07 ...Including a plurality of individual  
components in a repetitive configuration (EPO)  
257/E27.081 ....Including field-effect component (EPO)  
257/E27.084 .....Dynamic random access memory, DRAM,  
structure (EPO)  
257/E27.085 .....One-transistor memory cell structure,  
i.e., each memory cell containing only one transistor (EPO)  
  
257/E27.092 .....Capacitor in trench (EPO)

5 257/305 (0 OR, 5 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 (E) FIELD EFFECT Device

257/288 (E) Having insulated electrode (e.g., MOSFET,  
MOS diode)

257/296 (E) Insulated gate capacitor or insulated  
gate transistor combined with capacitor (e.g., dynamic  
memory cell)

257/301 ...Capacitor in trench

257/305 ....With means to insulate adjacent storage  
nodes (e.g., channel stops or field oxide)

5 257/E27.085 (0 OR, 5 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E27.001 DEVICE CONSISTING OF A PLURALITY OF  
SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR  
ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE  
(EPO)

257/E27.009 ...Including semiconductor component with at  
least one potential barrier or surface barrier adapted for  
rectifying, oscillating, amplifying, or switching, or  
including integrated passive circuit elements (EPO)

257/E27.01 ...With semiconductor substrate only (EPO)

257/E27.07 ...Including a plurality of individual  
components in a repetitive configuration (EPO)

257/E27.081 ....Including field-effect component (EPO)

257/E27.084 .....Dynamic random access memory, DRAM,  
structure (EPO)

257/E27.085 .....One-transistor memory cell structure,  
i.e., each memory cell containing only one transistor (EPO)

4 257/300 (1 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 (E) FIELD EFFECT Device

257/288 (E) Having insulated electrode (e.g., MOSFET,  
MOS diode)

257/296 (E) Insulated gate capacitor or insulated  
gate transistor combined with capacitor (e.g., dynamic  
memory cell)

257/300 ...Capacitor coupled to, or forms gate of,  
insulated gate field effect transistor (e.g.,  
nondestructive readout dynamic memory cell structure)

PLUS Search Results for S/N 10/064.869. Searched February 20, 2003 (Top 50)

|         |         |         |         |         |
|---------|---------|---------|---------|---------|
| 4785337 | 5999440 | 4388121 | 4763181 | 4999811 |
| 4833094 | 6207493 | 4574465 | 5442211 | 5365477 |
| 5384789 | 4791610 | 4883543 | 5618745 | 5508542 |
| 4830978 | 5798545 | 5208657 | 6194311 | 5635419 |
| 4910567 | 5317540 | 5300450 | 5465249 | 5671182 |
| 4916524 | 5432733 | 5334548 | 5872373 | 5736761 |
| 5198383 | 6136652 | 5383150 | 6151244 | 5770510 |
| 5364808 | 4864375 | 5559734 | 4761385 | 5866928 |
| 5468980 | 4980734 | 5753420 | 4786954 | 5959322 |
| 5973952 | 5640350 | 5999439 | 4864374 | 6066870 |